# **ON Semiconductor**

# Is Now



To learn more about onsemi™, please visit our website at www.onsemi.com

onsemi and Onsemi. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application,

# Octal D-Type Flip-Flop with 3-State Output

The MC74VHC374 is an advanced high speed CMOS octal flip-flip with 3-state output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This 8-bit D-type flip-flop is controlled by a clock input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

#### **Features**

- High Speed:  $f_{max} = 185 \text{ MHz}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V<sub>OLP</sub> = 0.9 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 266 FETs or 66.5 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant



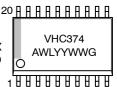
## ON Semiconductor®

http://onsemi.com

#### **MARKING DIAGRAMS**

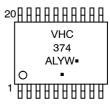


SOIC-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E





SOEIAJ-20 M SUFFIX CASE 967

VHC374 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74VHC374DWR2G	SOIC-20	1000 Units/Reel
MC74VHC374DTR2G	TSSOP-20	2500 Units/T&R
MC74VHC374MELG	SOEIAJ-20	2000 Units/Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

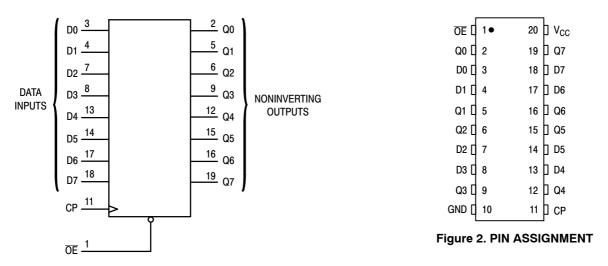


Figure 1. LOGIC DIAGRAM

## **FUNCTION TABLE**

	INPUTS	OUTPUT	
ŌĒ	СР	q	
L L L	- - - - L, H, \_ - X	H L X	H L No Change Z

#### **MAXIMUM RATINGS\***

Symbol	Paramete	r	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage		- 0.5 to + 7.0	V
V <sub>out</sub>	DC Output Voltage	- 0.5 to V <sub>CC</sub> + 0.5	V	
I <sub>IK</sub>	Input Diode Current	- 20	mA	
I <sub>OK</sub>	Output Diode Current	± 20	mA	
I <sub>out</sub>	DC Output Current, per Pin		± 25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and G	ND Pins	± 75	mA
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature		- 65 to + 150	°C

Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

# TSSOP Package: - 6.1 mW/°C from 65° to 125°C

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage			5.5	V
V <sub>in</sub>	DC Input Voltage	0	5.5	V	
V <sub>out</sub>	DC Output Voltage	0	$V_{CC}$	V	
T <sub>A</sub>	Operating Temperature		- 40	+ 85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time V <sub>CC</sub> V <sub>CC</sub>	= 3.3V = 5.0V	0	100 20	ns/V

#### DC ELECTRICAL CHARACTERISTICS

			Vcc		T <sub>A</sub> = 25°C		$T_A = -40$	0 to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V <sub>CC</sub> x 0.7			1.50 V <sub>CC</sub> x 0.7		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V <sub>CC</sub> x 0.3		0.50 V <sub>CC</sub> x 0.3	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$V_{in} = V_{IH} \text{ or } V_{IL} \\ I_{OH} = -4mA \\ I_{OH} = -8mA$	3.0 4.5	2.58 3.94			2.48 3.80		
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44	

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND  $\leq$  (V<sub>in</sub> or V<sub>out</sub>)  $\leq$  V<sub>CC</sub>.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

<sup>†</sup>Derating — SOIC Packages: - 7 mW/°C from 65° to 125°C

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub> T <sub>A</sub> = 3		T <sub>A</sub> = 25°C		T <sub>A</sub> = - 40 to 85°C		
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = 5.5V or GND	0 to 5.5			± 0.1		± 1.0	μА
l <sub>oz</sub>	Maximum Three-State Leakage Current	$V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	5.5			± 0.25		± 2.5	μА
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0	μА

## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

					T <sub>A</sub> = 25°C		T <sub>A</sub> = - 4		
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle)	$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$	80 55	130 85		70 50		ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$	130 85	185 120		110 75		
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, CP to Q	$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		8.1 10.6	12.7 16.2	1.0 1.0	15.0 18.5	ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		5.4 6.9	8.1 10.1	1.0 1.0	9.5 11.5	
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time, OE to Q	$\begin{aligned} V_{CC} &= 3.3 \pm 0.3 V \\ R_L &= 1 k \Omega \end{aligned}$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		7.1 9.6	11.0 14.5	1.0 1.0	13.0 16.5	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		5.1 6.6	7.6 9.6	1.0 1.0	9.0 11.0	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time, OE to Q	$\begin{aligned} V_{CC} &= 3.3 \pm 0.3 V \\ R_L &= 1 k \Omega \end{aligned}$	C <sub>L</sub> = 50pF		10.2	14.0	1.0	16.0	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	C <sub>L</sub> = 50pF		6.1	8.8	1.0	10.0	
t <sub>OSLH</sub> , t <sub>OSHL</sub>	Output to Output Skew	V <sub>CC</sub> = 3.3 ± 0.3V (Note 1)	C <sub>L</sub> = 50pF			1.5		1.5	ns
		V <sub>CC</sub> = 5.0 ± 0.5V (Note 1)	C <sub>L</sub> = 50pF			1.0		1.0	ns
C <sub>in</sub>	Maximum Input Capacitance				4	10		10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State)				6				pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0V	
$C_{PD}$	Power Dissipation Capacitance (Note 2)	32	pF

Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>PLHm</sub> - t<sub>PLHn</sub>|, t<sub>OSHL</sub> = |t<sub>PHLm</sub> - t<sub>PHLn</sub>|.
 C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/8 (per flip-flop). C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

## NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T <sub>A</sub> = 25°C		
Symbol	Parameter	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.6	0.9	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>		- 0.9	V
$V_{IHD}$	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V

## **TIMING REQUIREMENTS** (Input $t_r = t_f = 3.0 \text{ns}$ )

			T <sub>A</sub> = 25°C		T <sub>A</sub> = - 40 to 85°C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t <sub>w</sub>	Minimum Pulse Width, CP	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		5.0 5.0	5.5 5.0	ns
t <sub>su</sub>	Minimum Setup Time, D to CP	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		4.5 3.0	4.5 3.0	ns
t <sub>h</sub>	Minimum Hold Time, D to CP	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		2.0 2.0	2.0 2.0	ns
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$				ns

## **SWITCHING WAVEFORMS**

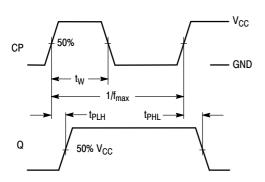


Figure 3.

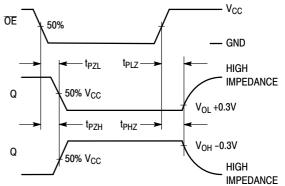


Figure 4.

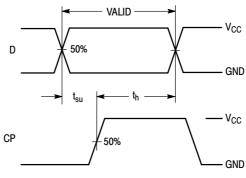
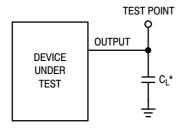
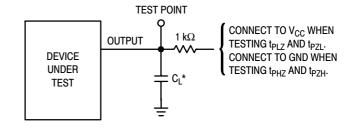


Figure 5.

## **TEST CIRCUITS**





\*Includes all probe and jig capacitance

\*Includes all probe and jig capacitance

Figure 6.

Figure 7.

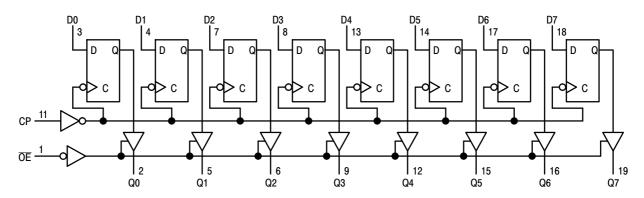


Figure 8. EXPANDED LOGIC DIAGRAM

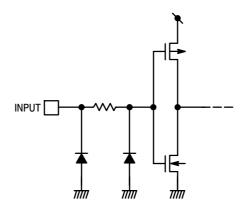
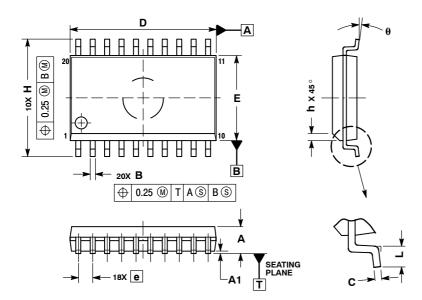


Figure 9. INPUT EQUIVALENT CIRCUIT

## **PACKAGE DIMENSIONS**

## SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



#### NOTES:

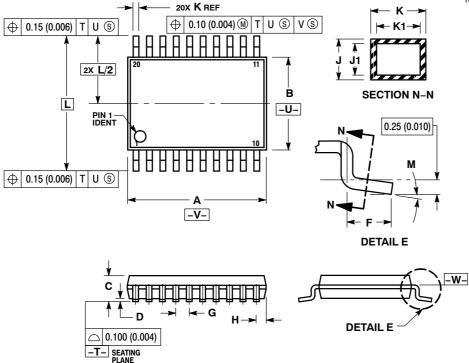
- NOTES:

  1. DIMENSIONS ARE IN MILLIMETERS.
  2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
  5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS					
DIM	MIN	MAX				
Α	2.35	2.65				
A1	0.10	0.25				
В	0.35	0.49				
С	0.23	0.32				
D	12.65	12.95				
E	7.40	7.60				
е	1.27	BSC				
Н	10.05	10.55				
h	0.25	0.75				
L	0.50	0.90				
θ	0°	7 °				

#### PACKAGE DIMENSIONS

## TSSOP-20 CASE 948E-02 **ISSUE C**



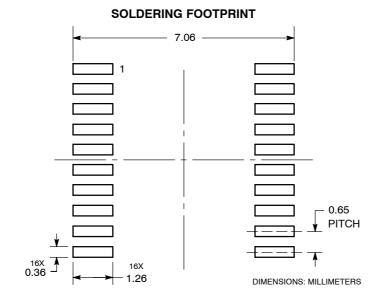
#### NOTES:

- 71ES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

- MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE
- DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
  DIMENSION AT MAXIMUM MATERIAL CONDITION.
  6. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

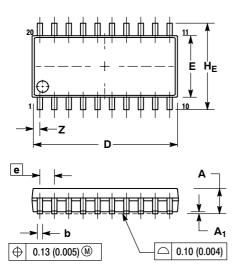
  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE —W—.

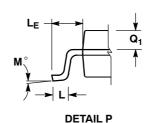
DETENTIONED AT DATON FLAINE -VI					
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С	-	1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252	BSC	
M	0°	8°	0°	8°	

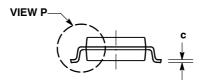


#### PACKAGE DIMENSIONS

SOEIAJ-20 CASE 967-01 **ISSUE A** 







#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
- B. DIMENSIONS D AND E DO NOT INCLUDE
  MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY
- 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
  TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.
  DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.15	0.25	0.006	0.010
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		0.81		0.032

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and are registered readerlands of semiconductor Components industries, Ite (SCILLC) and the series are injected to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

MC74VHC374/D